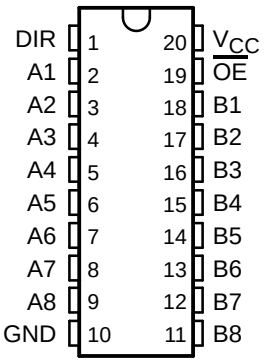
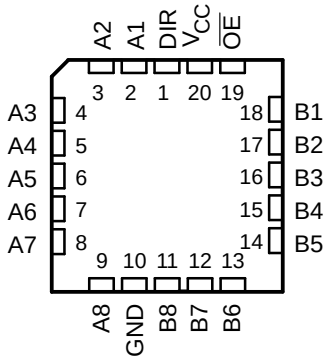
- **Inputs Are TTL-Voltage Compatible**
- ***EPIC***™ **(Enhanced-Performance Implanted CMOS) 1-μm Process**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), and DIP (N), Ceramic Chip Carriers (FK), Flat (W), and DIP (J) Packages**

SN54ACT245 . . . J OR W PACKAGE
SN74ACT245 . . . DB, DW, N, OR PW PACKAGE
(TOP VIEW)



SN54ACT245 . . . FK PACKAGE
(TOP VIEW)



description

These octal bus transceivers are designed for asynchronous two-way communication between data buses. The control-function implementation minimizes external timing requirements.

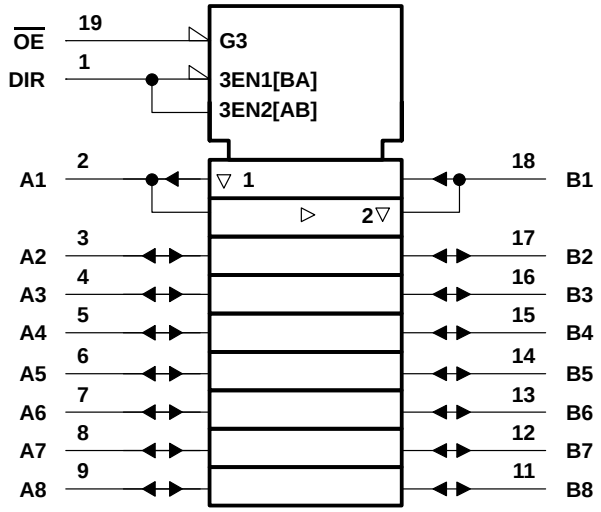
When the output-enable ($\overline{OE}$) is low, the device passes noninverted data from the A bus to the B bus or from the B bus to the A bus, depending upon the logic level at the direction control (DIR) input. A high on $\overline{OE}$ disables the device so that the buses are effectively isolated.

The SN54ACT245 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74ACT245 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

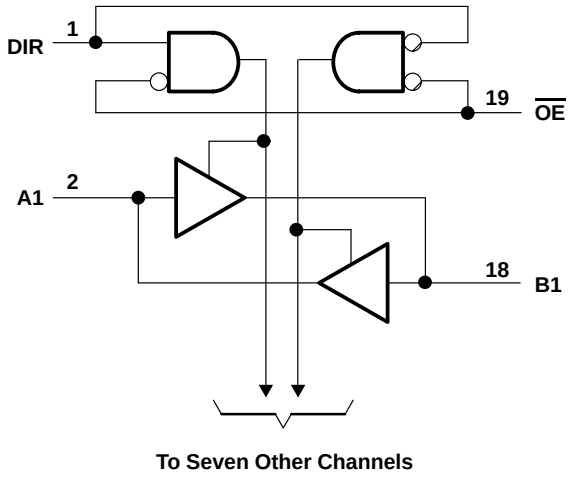
INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} . . . . . −0.5 V to 7 V
Input voltage range, V_I (see Note 1) . . . . . −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Note 1) . . . . . −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0 or V_I > V_{CC}) . . . . . ±20 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±20 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through V_{CC} or GND . . . . . ±200 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 2): DB package . . . . . 0.6 W
DW package . . . . . 1.6 W
PW package . . . . . 0.7 W
N package . . . . . 1.3 W
Storage temperature range, T_{stg} . . . . . −65°C to 150°C

‡ Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils, except for the N package, which has a trace length of zero.

recommended operating conditions (see Note 3)

		SN54ACT245		SN74ACT245		UNIT
		MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	4.5	5.5	4.5	5.5	V
V_{IH}	High-level input voltage	2		2		V
V_{IL}	Low-level input voltage		0.8		0.8	V
V_I	Input voltage	0	V_{CC}	0	V_{CC}	V
V_O	Output voltage	0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current		–24		–24	mA
I_{OL}	Low-level output current		24		24	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	0	8	0	8	ns/V
T_A	Operating free-air temperature	– 55	125	– 40	85	°C

NOTE 3: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V_{CC}	T_A = 25°C			SN54ACT245		SN74ACT245		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
V_{OH}		I_{OH} = – 50 μA	4.5 V	4.4	4.49		4.4		4.4		V
			5.5 V	5.4	5.49		5.4		5.4		
		I_{OH} = – 24 mA	4.5 V	3.88			3.7		3.76		
			5.5 V	4.86			4.7		4.76		
		I_{OH} = –50 mA†	5.5 V				3.85				
		I_{OH} = –75 mA†	5.5 V						3.85		
V_{OL}		I_{OL} = 50 μA	4.5 V		.001	0.1		0.1		0.1	V
			5.5 V		.001	0.1		0.1		0.1	
		I_{OL} = 24 mA	4.5 V			0.36		0.5		0.44	
			5.5 V			0.36		0.5		0.44	
		I_{OL} = 50 mA†	5.5 V					1.65			
		I_{OL} = 75 mA†	5.5 V							1.65	
I_{OZ}	A or B ports‡	$V_O = V_{CC}$ or GND	5.5 V			±0.5		±10		±5	μA
I_I	$\overline{OE}$ or DIR	$V_I = V_{CC}$ or GND	5.5 V			±0.1		±1		±1	μA
I_{CC}		$V_I = V_{CC}$ or GND, I_O = 0	5.5 V			4		80		40	μA
ΔI_{CC}§		One input at 3.4 V, Other inputs at GND or V_{CC}	5.5 V			0.6		1.6		1.5	mA
C_i		$V_I = V_{CC}$ or GND	5 V		4.5						pF
C_{io}		$V_O = V_{CC}$ or GND	5 V		15						pF

† Not more than one output should be tested at a time, and the duration of the test should not exceed 2 ms.
‡ For I/O ports, the parameter I_{OZ} includes the input leakage current.
§ This is the increase in supply current for each input that is at one of the specified TTL voltage levels rather than 0 V or V_{CC}.

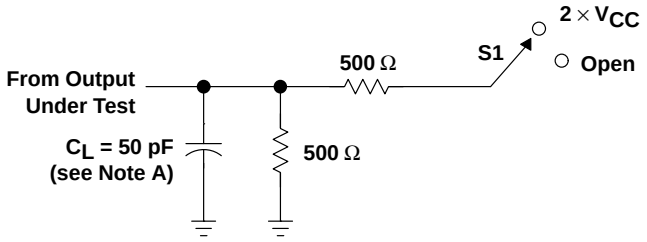
switching characteristics over recommended operating free-air temperature range, V_{CC} = 5 V ± 0.5 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	T_A = 25°C			SN54ACT245		SN74ACT245		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A or B	B or A	1	4	7.5	1	9	1.5	8	ns
t_{PHL}			1	4	8	1	10	1	9	
t_{PZH}	$\overline{OE}$	A or B	1	5	10	1	12	1.5	11	ns
t_{PZL}			1	5.5	10	1	13	1.5	12	
t_{PHZ}	$\overline{OE}$	A or B	1	5.5	10	1	12	1	11	ns
t_{PLZ}			1	5	10	1	12	1.5	11	

operating characteristics, V_{CC} = 5 V, T_A = 25°C

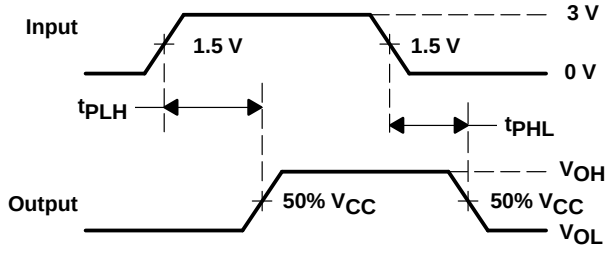
PARAMETER	TEST CONDITIONS	TYP	UNIT
C_{pd} Power dissipation capacitance per transceiver	C_L = 50 pF, f = 1 MHz	45	pF

PARAMETER MEASUREMENT INFORMATION

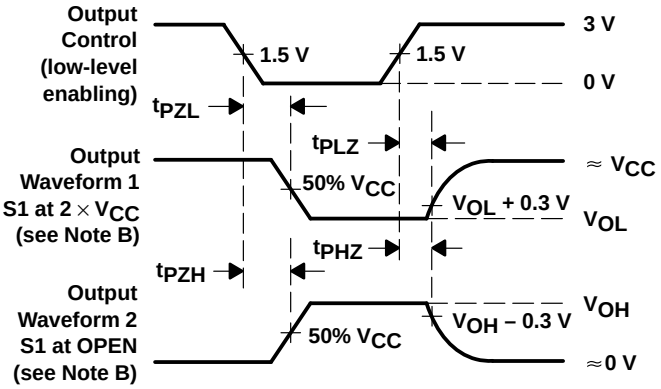


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	Open

LOAD CIRCUIT



VOLTAGE WAVEFORMS



VOLTAGE WAVEFORMS

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one input transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

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